

Features

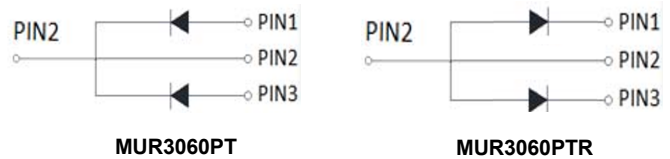
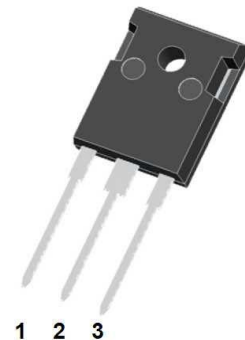
- Adopt FRED chip
- Low forward Voltage drop
- Fast reverse recovery time
- High frequency operation
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Guard ring for enhanced ruggedness and long term reliability

Typical Applications

- Typical applications are in switching power supplies, converters, freewheeling diodes, and reverse battery protection.

Mechanical Data

- **Package:** TO-247-3L
Molding compound meets UL 94 V-0 flammability rating, RoHS-compliant
- **Terminals:** Tin plated leads, solderable per J-STD-002 and JESD22-B102
- **Polarity:** As marked



■Maximum Ratings (T_j=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	MUR3060PT MUR3060PTR
Device marking code			MUR3060PT MUR3060 PTR
Repetitive Peak Reverse Voltage	VRRM	V	600
Average Rectified Output Current @60Hz sine wave, R-load, T _c (FIG.1)	I _O	A	30
Surge(Non-repetitive)Forward Current @60Hz half sine-wave, 1 cycle, T _j =25°C	I _{FSM}	A	300
Current Squared Time @1ms≤t≤8.3ms T _j =25°C,	I ² t	A ² s	93
Single Pulse Avalanche Energy @ Tp=40uS, T _j =25°C,L=15mH	EAS	mJ	140
Storage Temperature	T _{stg}	°C	-55 ~ +175
Junction Temperature	T _j	°C	-55 ~ +175
Typical Junction capacitance @4V,1MHz	C _j	pF	98



MUR3060PT MUR3060PTR

Ultra-Fast Recovery Diodes 15A*2



■ Electrical Characteristics (T_j=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	Min	Typ	Max	
Instantaneous forward voltage drop per diode	V _{FM}	V	I _{FM} =15.0A @ T _j =25°C	-	1.45	1.7	
			I _{FM} =15.0A @ T _j =150°C	-	1.25	1.4	
DC reverse current at rated DC blocking voltage per diode	I _{RRM1}	uA	V _{RM} =V _{RRM} T _j =25°C	-	-	5.0	
	I _{RRM2}		V _{RM} =V _{RRM} T _j =150°C	-	30	200	
Reverse Recovery Time	T _{RR}	ns	I _F =0.5A I _{RM} =1A I _{RR} =0.25A T _j =25°C	-	40	50	
			T _j =25°C		115		
			T _j =125°C		200		
Peak recovery current	I _{RRM}	A	T _j =25°C	I _F =15A di/dt=-200A/us V _{RM} =200V	-	5.0	-
			T _j =125°C		-	10.5	-
Reverse recovery charge	Q _{rr}	nC	T _j =25°C		-	285	-
			T _j =125°C		-	1000	-

■ Thermal Characteristics (T_a=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	
Thermal Resistance	Between junction and case	R _{θJ-C}	°C/W
	Between junction and Air	R _{θJ-A}	°C/W
			1.0
			50



■ Characteristics(Typical)

FIG1:Io -Tc Curve

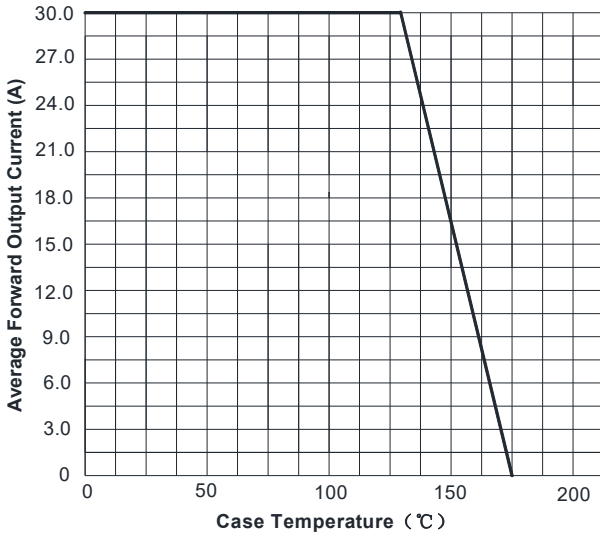


FIG2:Surge Forward Current Capability

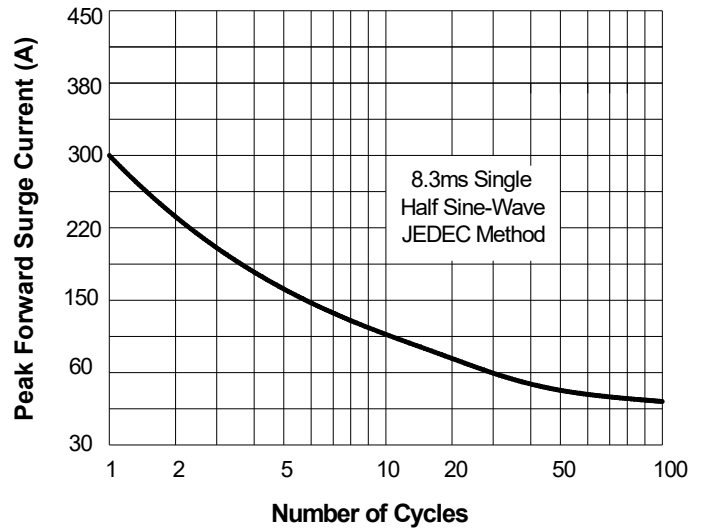


FIG3: Forward Voltage

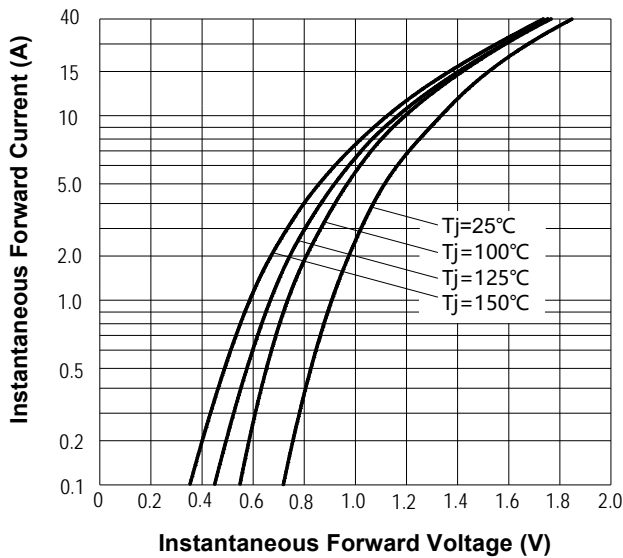


FIG.4: Instantaneous Reverse Characteristics

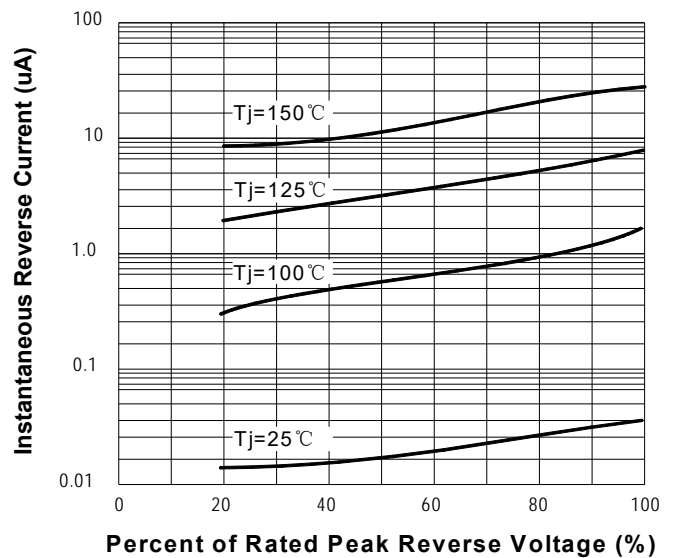
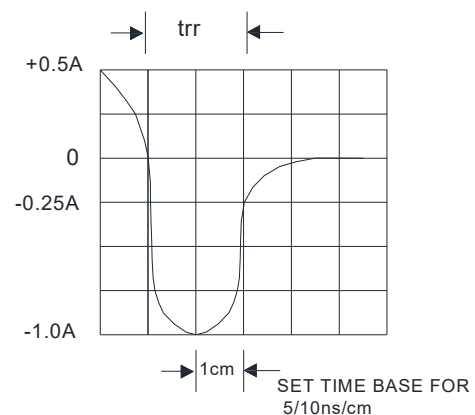
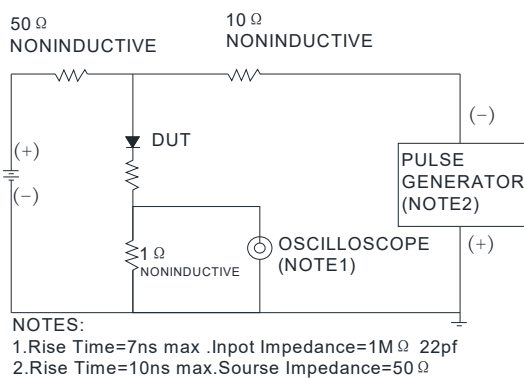
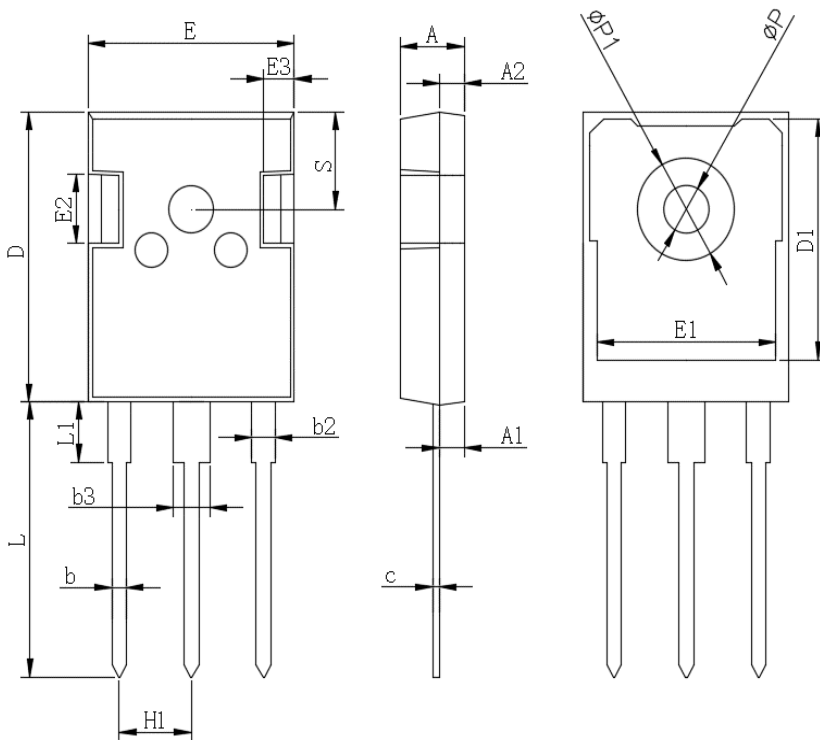


FIG.5: Diagram of circuit and Testing wave form of reverse recovery time





■ Outline Dimensions



TO-247-3L		
Dim	Min	Max
A	4.80	5.20
A1	2.21	2.61
A2	1.85	2.15
b	1.0	1.4
b2	1.91	2.21
C	0.5	0.7
D	20.70	21.30
D1	16.25	16.85
E	15.50	16.10
E1	13.0	13.6
E2	4.80	5.20
E3	2.30	2.70
L	19.62	20.22
L1	-	4.30
ΦP	3.40	3.80
ΦP1	-	7.30
S	6.15TYP	
H1	5.44TYP	
b3	2.80	3.20